Low Voltage, Rail-to-Rail Output Operational Amplifier

The NCS2003 is a low voltage operational amplifier with rail-to-rail output drive capability. The 1.8 V operation allows high performance operation in low voltage, low power applications.

Additional features include no output phase reversal with overdriven inputs, a low input offset voltage of 0.5 mV, ultra low input bias current of 1 pA, and a unity gain bandwidth of 5 MHz at 1.8 V. The tiny NCS2003 is the ideal solution for small portable electronic applications and is available in the space saving SOT23–5 and SOT–553 packages.

Features

- 7 MHz Unity Gain Bandwidth at 5 V
- 5 MHz Unity Gain Bandwidth at 1.8 V
- Rail-to-Rail Output
- No Output Phase Reversal for Over-Driven Input Signals
- Low Offset Voltage 500 μV typical
- Low Input Bias Current − 1 pA typical
- Space saving SOT23-5 and SOT553-5 Packages
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Cellular Telephones
- Current Shunt Monitors for battery monitoring
- Pulse Oximetry Signal Conditioning
- Blood Pressure Monitor Conditioning and Filtering
- Hard Drive Sensor Buffer



ON Semiconductor®

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SOT23-5 CASE 483-02

SOT553, 5 LEAD CASE 463B

MARKING DIAGRAMS





AN3 = NCS2003SN2T1G A3 = NCS2003XV53T2G

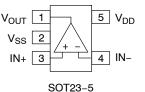
Y = Year

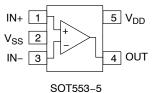
W = Work Week M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS





ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

ABSOLUTE MAXIMUM RATINGS

Over operating free-air temperature, unless otherwise stated

Parameter	Symbol	Limit	Unit
Supply Voltage (V _{DD} – V _{SS})	Vs	7	V
INPUT AND OUTPUT PINS			
Input Voltage (Note 1)	V _{IN}	V _{SS} – 300 mV to 7.0 V	V
Input Current	I _{IN}	10	mA
Output Short Circuit Current (Note 2)	I _{OSC}	100	mA
TEMPERATURE			
Storage Temperature	T _{STG}	-65 to 150	°C
Junction Temperature	T _J	150	°C
ESD RATINGS			
Human Body Model	HBM	2000	V
Machine Model	MM	200	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Neither input should exceed the range of VSS 300 mV to 7.0 V
- 2. Indefinite duration; however, maximum package power dissipation limits must be observed to ensure that the maximum junction temperature is not exceeded.

THERMAL INFORMATION (Note 3)

Thermal Metric	Symbol	Limit	Unit
Junction to Ambient – SOT23–5	$\theta_{\sf JA}$	235	°C/W
Junction to Ambient – SOT553–5	$\theta_{\sf JA}$	250	°C/W

^{3.} As mounted on an 80 x 80 x 1.5 mm FR4 PCB with 650 mm² and 2 oz (0.034 mm) thick copper heat spreader. Following JEDEC JESD/EIA 51.1, 51.2, 51.3 test guidelines.

OPERATING CONDITIONS

Parameter	Symbol	Limit	Unit
Operating Supply Voltage	V _S	1.7 to 5.5	V
Specified Operating Range	T _A	-40 to +85	°C

ELECTRICAL CHARACTERISTICS: $V_S = +1.8 \text{ V}$ **Boldface** limits apply over the specified temperature range, $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$. guaranteed by design and/or characterization. At $T_A = +25^{\circ}\text{C}$, $R_L = 10 \text{ k}\Omega$ connected to midsupply, $V_{CM} = V_{OUT} = \text{midsupply}$, unless otherwise noted.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	Vos			0.5	4.0	mV
					5.0	
Offset Voltage Drift	ΔV/ΔΤ			2.0		μV/°C
Input Bias Current	I _{IB}			1		рА
Input Offset Current	Ios			1		рА
Differential Input Resistance	R _{IN}			>1		TΩ
Differential Input Capacitance	C _{IN}			1.2		pF
Input Common Mode Range	V _{ICR}	Inferred from CMRR	V _{SS}		V _{DD} - 0.6	V
Common Mode Rejection Ratio	CMRR	V _{IN} = 0 V to V _{DD} - 0.6 V	70	80		dB
		V _{IN} = 0.2 V to V _{DD} – 0.6 V	65			
OUTPUT CHARACTERISTICS				1		
Output Voltage High	V _{OH}	$V_{ID} = +0.5 \text{ V}, R_L = 10 \text{ k}\Omega$	1.75	1.798		V
			1.75			
		V_{ID} = +0.5 V, R_L = 2 k Ω	1.7	1.78		
			1.7			
Output Voltage Low	V _{OL}	V_{ID} = -0.5 V, R_L = 10 k Ω		7.0	50	mV
					50	
		$V_{ID} = -0.5 \text{ V}, R_L = 2 \text{ k}\Omega$		20	100	
					100	
Short Circuit Current	I _{SC}	$V_{ID} = +0.5 \text{ V}, V_O = V_{SS}, \text{ Sourcing}$	5.0	8.0		mA
		$V_{ID} = -0.5 \text{ V}, V_O = V_{DD}, \text{ Sinking}$	10	14		
NOISE PERFORMANCE						
Voltage Noise Density	e _N	f = 1 kHz		25		nV/√Hz
Current Noise Density	i _N	f = 1 kHz		0.1		pA/√Hz
DYNAMIC PERFORMANCE	-		•	-		
Open Loop Voltage Gain	A _{VOL}	$R_L = 10 \text{ k}\Omega$	80	92		dB
			75			
		$R_L = 2 k\Omega$		92		dB
			70			
Gain Bandwidth Product	GBWP			5		MHz
Gain Margin	A _M	R_L = 10 k Ω , C_L = 5 pF		12		dB
Phase Margin	Ψм	$R_L = 10 \text{ k}\Omega$, $C_L = 5 \text{ pF}$		53		0
Slew Rate	SR	Positive Slope, R _L = 2 k, A _V = +1		6		V/μs
		Negative Slope, R _L = 2 k, A _V = +1		9		V/μs
Total Harmonic Distortion +	THD+N	$V_{O} = 1 \text{ Vpp, } R_{L} = 2 \text{ k}\Omega, A_{V} = +1, 1 \text{ kHz}$		0.015		%
Noise		$V_O = 1$ Vpp, $R_L = 2$ kΩ, $A_V = +1$, 10 kHz		0.025		%
POWER SUPPLY				1		
Power Supply Rejection Ratio	PSRR		72	80		dB
•			65			
Quiescent Current	I _{CC}	No Load		230	560	μΑ
	1	1	1	1		

ELECTRICAL CHARACTERISTICS: $V_S = +5.0 \text{ V}$ Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$. guaranteed by design and/or characterization. At $T_A = +25^{\circ}\text{C}$, $R_L = 10 \text{ k}\Omega$ connected to midsupply, $V_{CM} = V_{OUT} = \text{midsupply}$, unless otherwise noted.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS	•					
Offset Voltage	Vos			0.5	4.0	mV
					5.0	
Offset Voltage Drift	ΔV/ΔΤ			2.0		μV/°C
Input Bias Current	I _{IB}			1		рА
Input Offset Current	Ios			1		рА
Differential Input Resistance	R _{IN}			>1		TΩ
Differential Input Capacitance	C _{IN}			1.2		pF
Input Common Mode Range	V _{ICR}	Inferred from CMRR	V _{SS}		V _{DD} - 0.6	V
Common Mode Rejection Ratio	CMRR	V _{IN} = 0 V to V _{DD} – 0.6 V	65	70		dB
		V _{IN} = 0.2 V to V _{DD} – 0.6 V	63			
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	$V_{ID} = +0.5 \text{ V}, R_L = 10 \text{ k}\Omega$	4.95	4.99		V
			4.95			
		V_{ID} = +0.5 V, R_L = 2 k Ω	4.9	4.97		
			4.9			
Output Voltage Low	V _{OL}	V_{ID} = -0.5 V, R_L = 10 k Ω		8.0	50	mV
					50	
		$V_{ID} = -0.5 \text{ V}, R_L = 2 \text{ k}\Omega$		24	100	
					100	
Short Circuit Current	Circuit Current I _{SC} V _{ID} =	$V_{ID} = +0.5 \text{ V}, V_O = V_{SS}, \text{ Sourcing}$	40	76		mA
		$V_{ID} = -0.5 \text{ V}, V_O = V_{DD}, \text{ Sinking}$	50	96		
NOISE PERFORMANCE						
Voltage Noise Density	e _N	f = 1 kHz		25		nV/√Hz
Current Noise Density	i _N	f = 1 kHz		0.2		pA/√Hz
DYNAMIC PERFORMANCE						
Open Loop Voltage Gain	A _{VOL}	$R_L = 10 \text{ k}\Omega$	86	92		dB
		_	78			
		$R_1 = 2 k\Omega$	83	92		dB
		_	78			
Gain Bandwidth Product	GBWP			7.0		MHz
Total Harmonic Distortion +	THD+N	$V_O = 4Vpp, R_L = 2 k\Omega, A_V = +1, 1 kHz$		0.005		%
Noise		$V_0 = 4Vpp, R_L = 2 k\Omega, A_V = +1, 10 kHz$		0.01		%
Gain Margin	A _M	$R_L = 10 \text{ k}\Omega$, $C_L = 5 \text{ pF}$		9		dB
Phase Margin	Ψм	$R_L = 10 \text{ k}\Omega$, $C_L = 5 \text{ pF}$		64		· ·
Slew Rate	SR	Positive Slope, $R_L = 2 \text{ k, } A_V = +1$		7		V/μs
		Negative Slope, $R_L = 2 \text{ k}$, $A_V = +1$		14		V/μs
POWER SUPPLY	1	2		1	1	- , , , , ,
Power Supply Rejection Ratio	PSRR	<u> </u>	72	80		dB
capp.,joolon natio	. 5		65	35		30
Quiescent Current	I _{CC}	No Load		300	660	μΑ
	.00			1	1	mA

TYPICAL CHARACTERISTICS

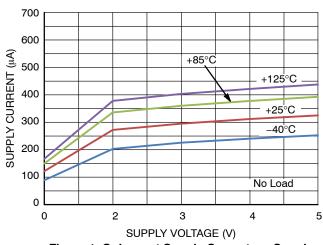


Figure 1. Quiescent Supply Current vs. Supply Voltage

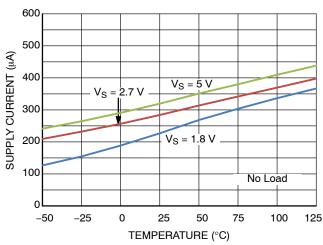


Figure 2. Quiescent Supply Current vs. Temperature

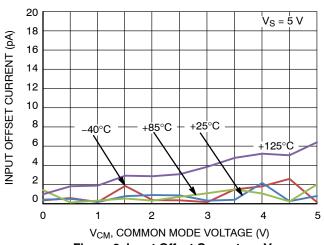


Figure 3. Input Offset Current vs. V_{CM}

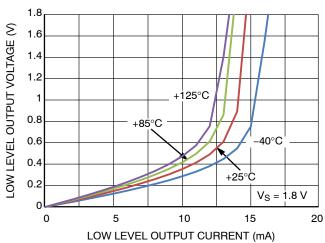


Figure 4. Low Level Output Voltage vs. Output Current @ $V_S = 1.8 \text{ V}$

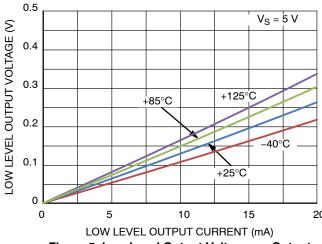


Figure 5. Low Level Output Voltage vs. Output Current @ $V_S = 5 V$

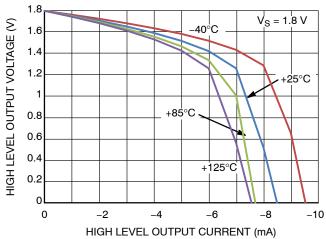


Figure 6. High Level Output Voltage vs. Output Current @ V_S = 1.8 V

TYPICAL CHARACTERISTICS

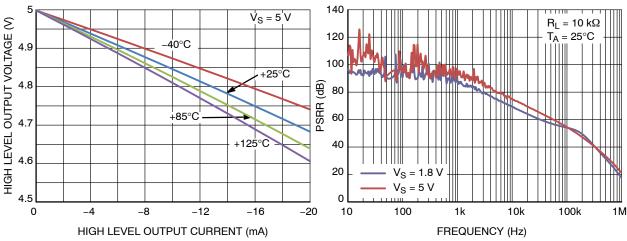


Figure 7. High Level Output Voltage vs. Output Current @ $V_S = 5 \text{ V}$

Figure 8. PSRR vs. Frequency

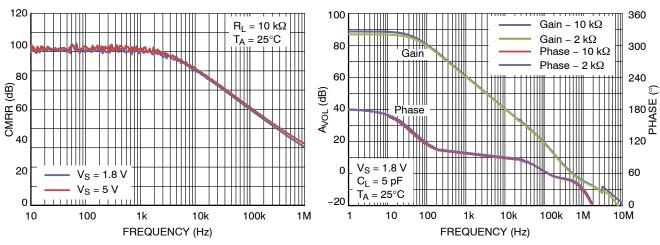


Figure 9. CMRR vs. Frequency

Figure 10. Open Loop Gain and Phase vs. Frequency @ $V_S = 1.8 \text{ V}$

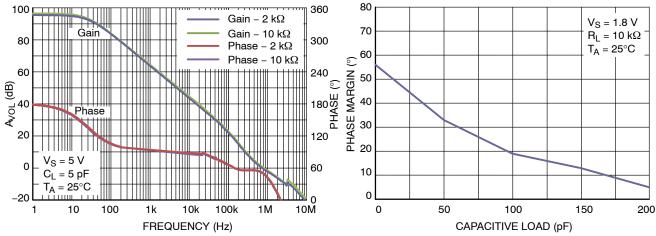
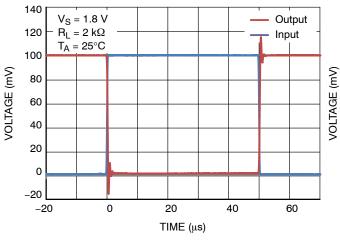


Figure 11. Open Loop Gain and Phase vs. Frequency @ $V_S = 5 \text{ V}$

Figure 12. Phase Margin vs. Capacitive Load

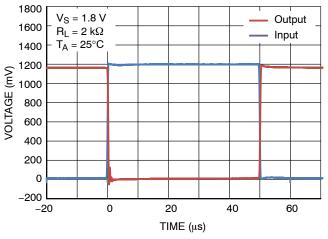
TYPICAL CHARACTERISTICS



Output $V_S = 1.8 V$ 120 $R_L = 2 k\Omega$ Input T_A = 25°C 100 80 60 40 20 0 -20 -20 20 40 60 TIME (µs)

Figure 13. Inverting Small Signal Transient Response

Figure 14. Non-Inverting Small Signal Transient Response



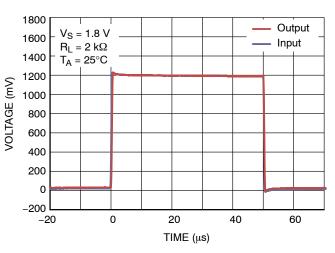
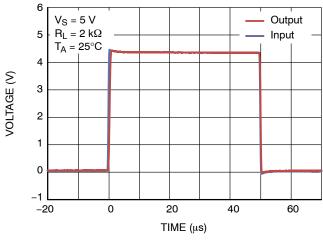


Figure 15. Inverting Large Signal Transient Response

Figure 16. Non-Inverting Large Signal Transient Response



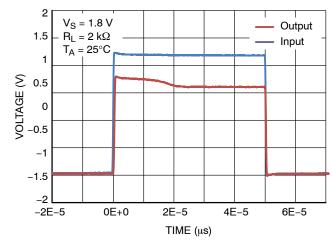
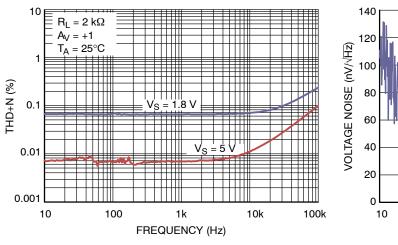


Figure 17. Non-Inverting Large Signal Transient Response

Figure 18. Output Overload Recovery

TYPICAL CHARACTERISTICS



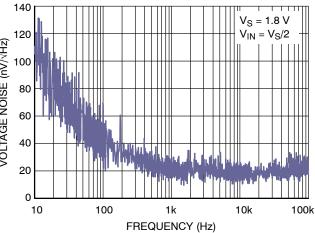


Figure 19. THD+N vs. Frequency

Figure 20. Input Voltage Noise vs. Frequency

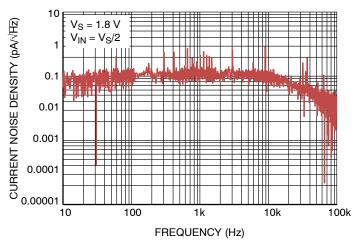


Figure 21. Noise Density vs. Frequency

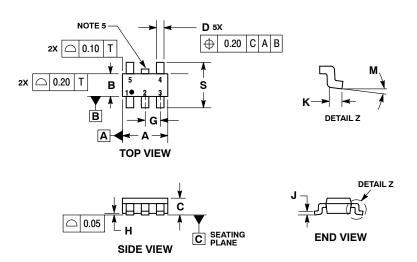
ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NCS2003SN2T1G	AN3	SOT23-5 (Pb-Free)	3000 / Tape and Reel
NCS2003XV53T2G	А3	SOT553-5 (Pb-Free)	4000 / Tape and Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 ISSUE K



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

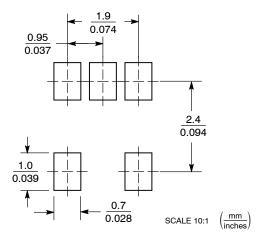
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS. SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.

 5. OPTIONAL CONSTRUCTION: AN ADDITIONAL
 - OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS				
DIM	MIN MAX				
Α	3.00	BSC			
В	1.50	BSC			
С	0.90	1.10			
D	0.25	0.50			
G	0.95	BSC			
Н	0.01	0.10			
J	0.10	0.26			
K	0.20	0.60			
M	0 °	10°			
S	2.50 3.00				

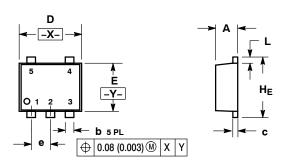
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-553, 5 LEAD CASE 463B ISSUE C

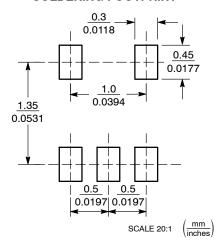


NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	М	MILLIMETERS INCHES				
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
е		0.50 BSC		0.020 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.55	1.60	1.65	0.061	0.063	0.065

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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